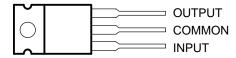
- 3-Terminal Regulators
- Output Current up to 500 mA
- No External Components
- Internal Thermal-Overload Protection
- High Power-Dissipation Capability
- Internal Short-Circuit Current Limiting
- Output Transistor Safe-Area Compensation
- Direct Replacements for Fairchild μA78M00 Series

description

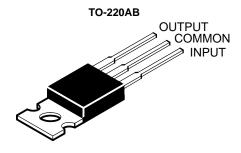
This series of fixed-voltage integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. Each of these regulators can deliver up to 500 mA of output current. The internal current-limiting and thermal-shutdown features of these regulators essentially make them immune to overload. In addition to use as fixed-voltage regulators, these devices can be used with external components to obtain adjustable output voltages and currents and also as the power-pass element in precision regulators.

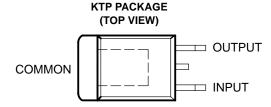
The $\mu A78M00C$ series is characterized for operation over the virtual junction temperature range of 0°C to 125°C.

KC PACKAGE (TOP VIEW)



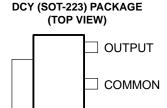
The COMMON terminal is in electrical contact with the mounting base.

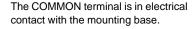




The COMMON terminal is in electrical contact with the mounting base.









Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



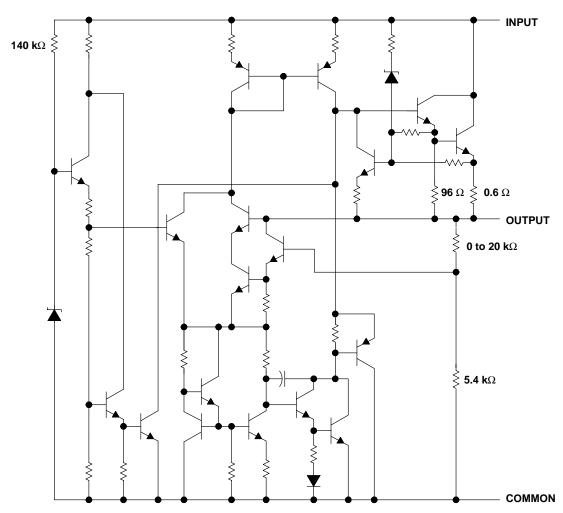
INPUT

AVAILABLE OPTIONS

			PACKAGED DEVIC	ES
TJ	V _O (NOM) (V)	SOT-223 (DCY)	HEAT-SINK MOUNTED (KC)	PLASTIC FLANGE MOUNTED (KTP)
	3.3	μΑ78M33CDCY	μΑ78M33CKC	μΑ78M33CKTP
	5	μΑ78M05CDCY	μΑ78M05CKC	μΑ78M05CKTP
	6	-	_	μΑ78M06CKTP
0°C to 125°C	8	μΑ78M08CDCY	μΑ78M08CKC	μΑ78M08CKTP
0 0 10 120 0	9	-	_	μΑ78M09CKTP
	10	-	μΑ78M10CKC	μΑ78M10CKTP
	12	_	μΑ78M12CKC	μΑ78M12CKTP
	15	_	-	μΑ78M15CKTP

The KTP package is only available taped and reeled. Add the suffix R to the device type (e.g., μ A78M05CKTPR). The DCY package is also available taped and reeled.

schematic



Resistor values shown are nominal.



absolute maximum ratings over virtual junction temperature range (unless otherwise noted)†

Input voltage, V _I	35 V
Package thermal impedance, θ _{JA} (see Notes 1 and 2): DCY package	49°C/W
(see Notes 1 and 3): KC package	25°C/W
(see Notes 1 and 2): KTP package	28°C/W
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C
Virtual junction temperature range, T _J	0°C to 150°C
Storage temperature range, T _{Stg}	-65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) T_A)/\theta_{JA}$. Selecting the maximum of 150°C can affect reliability.
 - 2. The package thermal impedance is calculated in accordance with JESD 51-5.
 - 3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions

			MIN	MAX	UNIT
		μA78M33	5.3	25	
		μΑ78Μ05	7	5.3 25 7 25 8 25 10.5 25 11.5 26 12.5 28 14.5 30	
		μA78M06	5.3 25 7 25 8 25 10.5 25 11.5 26 12.5 28 14.5 30 17.5 30		
 	lanut voltage	μA78M08	10.5	25	V
٧ı	Input voltage	μ Α78 Μ09	11.5	26	V
		μ Α78M1 0	12.5	28	
		μA78M12	14.5	30	
		μA78M15	17.5	30	
lo	Output current			500	mA
TJ	Operating virtual junction temperature		0	125	°C

electrical characteristics at specified virtual junction temperature, $V_I = 8 \text{ V}$, $I_O = 350 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER		a constraint	μ Α	78M330	3	UNIT
PARAMETER	TES	ST CONDITIONS†	MIN	TYP	MAX	UNIT
Output walks as t	V _I = 8 V to 20 V		3.2	3.3	3.4	٧
Output voltage‡	V = 8 V 10 20 V	$T_J = 0$ °C to 125°C	3.1	3.3	3.5	V
Input voltage regulation	lo - 200 mA	V _I = 5.3 V to 25 V		9	100	mV
Input voltage regulation	I _O = 200 mA	V _I = 8 V to 25 V		3	50	IIIV
Dinnle rejection	$V_{I} = 8 \text{ V to } 18 \text{ V},$	$I_O = 100 \text{ mA}, T_J = 0^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	62			dB
Ripple rejection	f = 120 Hz	I _O = 300 mA	62	80		uБ
Output voltage regulation	V _I = 8 V,	I _O = 5 mA to 500 mA		20	100	mV
Temperature coefficient of output voltage	$I_O = 5 \text{ mA},$	$T_J = 0$ °C to 125°C		-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz			40	200	μV
Dropout voltage				2		V
Bias current				4.5	6	mA
Dies surrent shangs	I _O = 200 mA,	$V_I = 8 \text{ V to } 25 \text{ V}, T_J = 0^{\circ}\text{C to } 125^{\circ}\text{C}$			0.8	A
Bias current change	$I_O = 5$ mA to 350 mA,	$T_J = 0$ °C to 125°C			0.5	mA
Short-circuit output current	V _I = 35 V			300		mA
Peak output current				700		mA

[†] All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, $V_I = 10 \text{ V}$, $I_O = 350 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER		a acupiricust	μ Α	78M050	;	UNIT
PARAMETER	TES	TEST CONDITIONS†			MAX	UNIT
Output and to me	V _I = 7 V to 20 V		4.8	5	5.2	V
Output voltage	V = 7 V to 20 V	$T_J = 0$ °C to 125°C	4.75		5.25	V
Input voltage regulation	lo - 200 mA	V _I = 7 V to 25 V		3	100	mV
Input voltage regulation	I _O = 200 mA	V _I = 8 V to 25 V		1	50	IIIV
Pinnle rejection	$V_{I} = 8 \text{ V to } 18 \text{ V},$	$I_O = 100 \text{ mA}, T_J = 0^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	62			dB
Ripple rejection	f = 120 Hz	I _O = 300 mA	62	80		uБ
Output voltage regulation	$I_O = 5 \text{ mA to } 500 \text{ mA}$			20	100	mV
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$	mA		10	50	IIIV
Temperature coefficient of output voltage	$I_O = 5 \text{ mA},$	$T_J = 0$ °C to 125°C		-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz			40	200	μV
Dropout voltage				2		V
Bias current				4.5	6	mA
Dies surrent change	I _O = 200 mA,	$V_{I} = 8 \text{ V to } 25 \text{ V}, T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$			0.8	mA
Bias current change	$I_O = 5 \text{ mA to } 350 \text{ mA},$	$T_J = 0$ °C to 125°C			0.5	IIIA
Short-circuit output current	V _I = 35 V			300		mA
Peak output current				0.7		Α

[†] All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.



[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, V_I = 11 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μ Α	78M060	3	UNIT
PARAMETER		MIN	TYP	MAX	UNIT		
Outoutualtana	I _O = 5 mA to 350 mA,	V _I = 8 V to 21 V		5.75	6	6.25	V
Output voltage	10 = 3 IIIA to 330 IIIA,	V = 0 V 10 21 V	$T_J = 0$ °C to 125°C	5.7		6.3	V
Input voltage regulation	In - 200 m/	V _I = 8 V to 25 V			5	100	mV
Input voltage regulation	I _O = 200 mA	V _I = 9 V to 25 V			1.5	50	IIIV
Ripple rejection	V _I = 9 V to 19 V,	f = 120 Hz	$I_O = 100 \text{ mA},$ $T_J = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	59			dB
., .		F	I _O = 300 mA	59	80		
Output voltage regulation	I _O = 5 mA to 500 mA				20	120	mV
Output voltage regulation	I _O = 5 mA to 200 mA				10	60	IIIV
Temperature coefficient of output voltage	I _O = 5 mA,	T _J = 0°C to 125°C			-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				45		μV
Dropout voltage					2		V
Bias current					4.5	6	mA
Dina aurrant abanca	V _I = 9 V to 25 V,	$I_O = 200 \text{ mA},$	T _J = 0°C to 125°C	125°C		0.8	A
Bias current change	$I_O = 5 \text{ mA to } 350 \text{ mA},$	$T_J = 0$ °C to 125°C				0.5	mA
Short-circuit output current	V _I = 35 V				270		mA
Peak output current					0.7		Α

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS			78M080	;	UNIT
PARAMETER		TEST CONDITIONS†		MIN	TYP	MAX	UNIT
Output wells we	V _I = 10.5 V to 23 V,	I _O = 5 mA to 350 mA		7.7	8	8.3	V
Output voltage	V = 10.5 V to 25 V,	10 = 3 IIIA to 330 IIIA	$T_J = 0^{\circ}C$ to $125^{\circ}C$	7.6		8.4	V
Input voltage regulation	In - 200 mA	V _I = 10.5 V to 25 V			6	100	mV
input voltage regulation	I _O = 200 mA	V _I = 11 V to 25 V			2	50	IIIV
Pinnle rejection	V _I = 11.5 V to 21.5 V,	I _O = 100 mA,	$T_J = 0$ °C to 125°C	56			dB
Ripple rejection	f = 120 Hz	I _O = 300 mA		56	80		uБ
Output voltage regulation	I _O = 5 mA to 500 mA				25	160	mV
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	80	IIIV
Temperature coefficient of output voltage	I _O = 5 mA,	$T_J = 0$ °C to 125°C			-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				52		μV
Dropout voltage					2		V
Bias current					4.6	6	mA
Diag assument about	V _I = 10.5 V to 25 V,	I _O = 200 mA,	T _J = 0°C to 125°C			0.8	A
Bias current change	$I_O = 5 \text{ mA to } 350 \text{ mA},$	T _J = 0°C to 125°C				0.5	mA
Short-circuit output current	V _I = 35 V				250		mA
Peak output current					0.7		Α

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.



electrical characteristics at specified virtual junction temperature, $V_I = 16 \text{ V}, I_O = 350 \text{ mA}, T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]			μ Α	78M090	;	UNIT
PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
Outrout walks as	V _I = 11.5 V to 24 V,	I _O = 5 mA to 350 mA		8.6	9	9.4	V
Output voltage	V = 11.5 V to 24 V,	10 = 3 IIIA to 330 IIIA	$T_J = 0^{\circ}C$ to $125^{\circ}C$	8.5		9.5	V
Input voltage regulation	I _O = 200 mA	V _I = 11.5 V to 26 V			6	100	mV
input voltage regulation	10 = 200 IIIA	V _I = 12 V to 26 V			2	50	IIIV
Pinnle rejection	V _I = 13 V to 23 V,	I _O = 100 mA,	$T_J = 0$ °C to 125°C	56			dB
Ripple rejection	f = 120 Hz	I _O = 300 mA		56	80		uБ
Output voltage regulation	$I_O = 5 \text{ mA to } 500 \text{ mA}$				25	180	mV
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	90	IIIV
Temperature coefficient of output voltage	I _O = 5 mA,	T _J = 0°C to 125°C			-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				58		μV
Dropout voltage					2		V
Bias current					4.6	6	mA
Dies surrent change	V _I = 11.5 V to 26 V,	I _O = 200 mA,	$T_J = 0^{\circ}C$ to $125^{\circ}C$			0.8	A
Bias current change	$I_{O} = 5 \text{ mA to } 350 \text{ mA},$	T _J = 0°C to 125°C				0.5	mA
Short-circuit output current	V _I = 35 V				250		mA
Peak output current					0.7		Α

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 17 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

DADAMETER	TEST CONDITIONS [†]			μA	78M10	С	UNIT
PARAMETER		MIN	TYP	MAX			
O trust valtage	V ₁ = 12.5 V to 25 V	lo = 5 m/ to 350 m/		9.6	10	10.4	V
Output voltage	$V_{I} = 12.5 \text{ V to } 25 \text{ V},$	$I_O = 5 \text{ mA to } 350 \text{ mA}$	$T_J = 0$ °C to 125°C	9.5		10.5	V
Input voltage regulation	I _O = 200 mA	V _I = 12.5 V to 28 V			7	100	mV
input voitage regulation	IO = 200 IIIA	V _I = 14 V to 28 V			2	50	IIIV
Pinnle rejection	V _I = 15 V to 25 V,	I _O = 100 mA,	$T_J = 0$ °C to 125°C	59			dB
Ripple rejection	f = 120 Hz	I _O = 300 mA		55	80		uБ
Output voltage regulation	I _O = 5 mA to 500 mA				25	200	mV
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	100	IIIV
Temperature coefficient of output voltage	I _O = 5 mA,	$T_J = 0$ °C to 125°C			-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				64		μV
Dropout voltage					2		V
Bias current					4.7	6	mA
Ding gurrant change	V _I = 12.5 V to 28 V,	I _O = 200 mA,	$T_J = 0^{\circ}C$ to $125^{\circ}C$			0.8	mA
Bias current change	$I_O = 5 \text{ mA to } 350 \text{ mA},$	T _J = 0°C to 125°C				0.5	IIIA
Short-circuit output current	V _I = 35 V				245		mA
Peak output current					0.7		Α

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.



electrical characteristics at specified virtual junction temperature, $V_I = 19 \text{ V}$, $I_O = 350 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]			μ Α	78M120		UNIT
PARAMETER	TEST CONDITIONS				TYP	MAX	UNII
Outrout walks as	V _I = 14.5 V to 27 V,	I _O = 5 mA to 350 mA		11.5	12	12.5	V
Output voltage	V = 14.5 V to 21 V,	10 = 3 IIIA to 330 IIIA	$T_J = 0$ °C to 125°C	11.4		12.6	V
Input voltage regulation	I _O = 200 mA	V _I = 14.5 V to 30 V			8	100	mV
input voltage regulation	10 = 200 IIIA	V _I = 16 V to 30 V			2	50	IIIV
Ripple rejection	V _I = 15 V to 25 V,	I _O = 100 mA,	$T_J = 0$ °C to 125°C	55			dB
Rippie rejection	aa F	I _O = 300 mA		55	80		иь
Output voltage regulation	I _O = 5 mA to 500 mA				25	240	mV
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	120	IIIV
Temperature coefficient of output voltage	I _O = 5 mA				-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				75		μV
Dropout voltage					2		V
Bias current					4.8	6	mA
Dies surrent shangs	V _I = 14.5 V to 30 V,	I _O = 200 mA,	$T_J = 0^{\circ}C$ to $125^{\circ}C$			0.8	mA
Bias current change	I _O = 5 mA to 350 mA,	T _J = 0°C to 125°C				0.5	mA
Short-circuit output current	V _I = 35 V				240		mA
Peak output current					0.7		Α

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 23 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA	78M15	2	UNIT
PARAMETER		TEST CONDITIONS!			TYP	MAX	UNII
Outrot well-ma	\/ı = 17.5 \/ to 20 \/	lo - 5 m \ to 250 m \		14.4	15	15.6	V
Output voltage	$V_{I} = 17.5 \text{ V to } 30 \text{ V},$	$I_O = 5 \text{ mA to } 350 \text{ mA}$	$T_J = 0$ °C to 125°C	14.25		15.75	v
Input voltage regulation	lo - 200 mA	V _I = 17.5 V to 30 V			10	100	mV
Input voltage regulation	I _O = 200 mA	V _I = 20 V to 30 V			3	50	IIIV
Pinnle rejection	V _I = 18.5 V to 28.5 V,	$I_O = 100 \text{ mA},$	$T_J = 0$ °C to 125°C	54			dB
Ripple rejection	f = 120 Hz	I _O = 300 mA		54	70		uБ
Output voltage regulation	$I_O = 5 \text{ mA to } 500 \text{ mA}$				25	300	mV
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	150	IIIV
Temperature coefficient of output voltage	I _O = 5 mA,	$T_J = 0^{\circ}C$ to $125^{\circ}C$			-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				90		μV
Dropout voltage					2		V
Bias current					4.8	6	mA
Diag gurrant shangs	V _I = 17.5 V to 30 V,	I _O = 200 mA,	$T_J = 0^{\circ}C$ to $125^{\circ}C$			0.8	mA
Bias current change	$I_O = 5 \text{ mA to } 350 \text{ mA},$	$T_J = 0^{\circ}C$ to $125^{\circ}C$				0.5	IIIA
Short-circuit output current	V _I = 35 V				240		mA
Peak output current					0.7		Α

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.



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